

Docket No.: 57454-329

#4/Pre-Am
5-2-02
PATENT
JD

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Masahiro SHIMIZU, et al.

Serial No.: Divisional of
Appln. Serial No. 09/452,099

Filed: January 24, 2002

For: SEMICONDUCTOR DEVICE

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Group Art Unit: To be assigned

Examiner: To be assigned

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, DC 20231

Sir:

Prior to examination of the above-referenced application, please amend the application as

follows:

IN THE TITLE:

Please change the title from "SEMICONDUCTOR DEVICE" to --INTEGRATED
CIRCUIT HAVING A MEMORY CELL TRANSISTOR WITH A GATE OXIDE LAYER
WHICH IS THICKER THAN THE GATE OXIDE LAYER OF A PERIPHERAL CIRCUIT
TRANSISTOR--

IN THE SPECIFICATION:

On page 1, after the title, please insert the following:

--This application is a divisional of U.S. Patent Application Serial No. 09/452,099, filed

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